

# RJK2555DPA

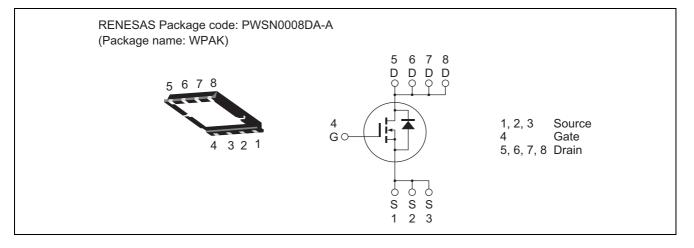
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1776-0200 Rev.2.00 Apr 09, 2009

# Features

- Low on-resistance
- Low drive current
- High density mounting

# Outline



# **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	250	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	17	А
Drain peak current	I <sub>D (pulse)</sub> Note1	34	А
Body-drain diode reverse drain current	I <sub>DR</sub>	17	А
Body-drain diode reverse drain peak current	Note1 I <sub>DR (pulse)</sub>	34	А
Avalanche current	I <sub>AP</sub> <sup>Note3</sup>	7	А
Avalanche energy	E <sub>AR</sub> <sup>Note3</sup>	3.0	mJ
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	۵°
Storage temperature	Tstg	-55 to +150	°C

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. Value at Tc = 25°C

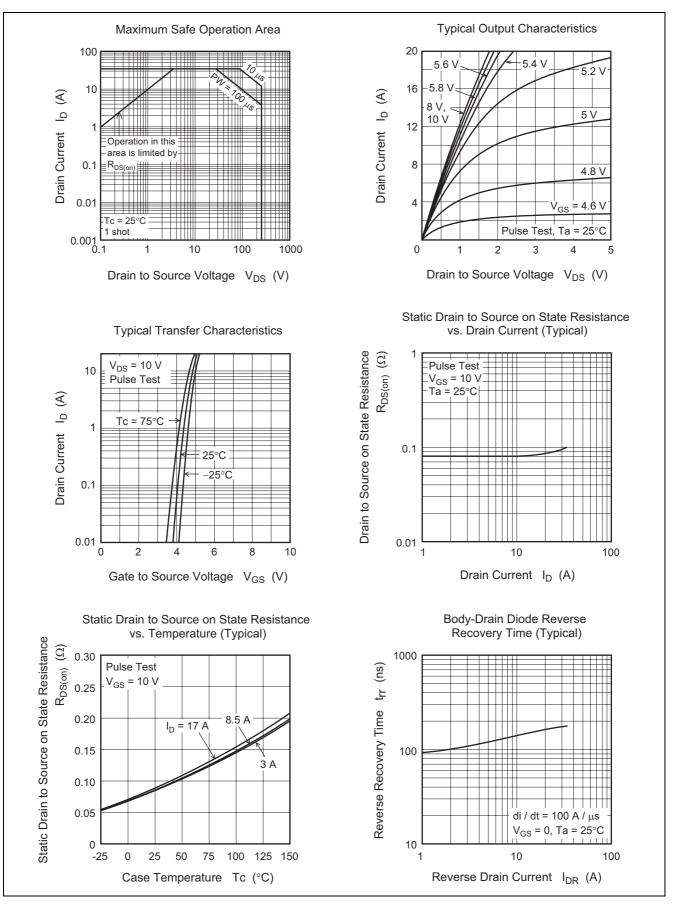
3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

# **Electrical Characteristics**

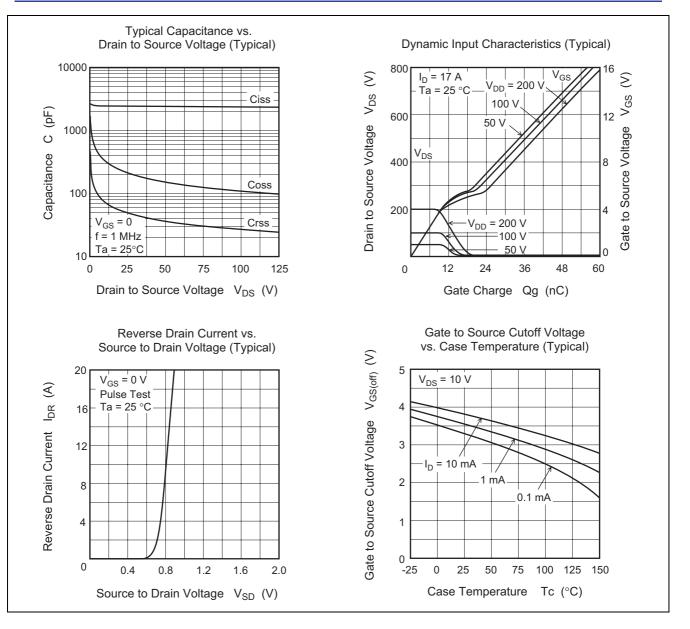
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	250	—		V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	—	1	μA	$V_{DS} = 250 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±1	μA	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	2.5	_	4.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	—	0.083	0.104	Ω	$I_D = 8.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance Input capacitance	Ciss		2400		pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss		2400		pF	$V_{\text{DS}} = 25 \text{ V}$ $V_{\text{GS}} = 0$ f = 1  MHz
Reverse transfer capacitance	Crss		49		pr pF	
Turn-on delay time	t <sub>d(on)</sub>	_	61	_	ns	I <sub>D</sub> = 8.5 A
Rise time	tr		42		ns	$V_{GS} = 10 V$ $R_L = 14.7 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	t <sub>d(off)</sub>		100		ns	
Fall time	t <sub>f</sub>		33		ns	
Total gate charge	Qg		39		nC	V <sub>DD</sub> = 200 V
Gate to source charge	Qgs		12.4		nC	V <sub>GS</sub> = 10 V I <sub>D</sub> = 17 A
Gate to drain charge	Qgd		10.5		nC	
Body-drain diode forward voltage	V <sub>DF</sub>	_	0.90	1.35	V	$I_F = 17 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	165	—	ns	$I_F = 17 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

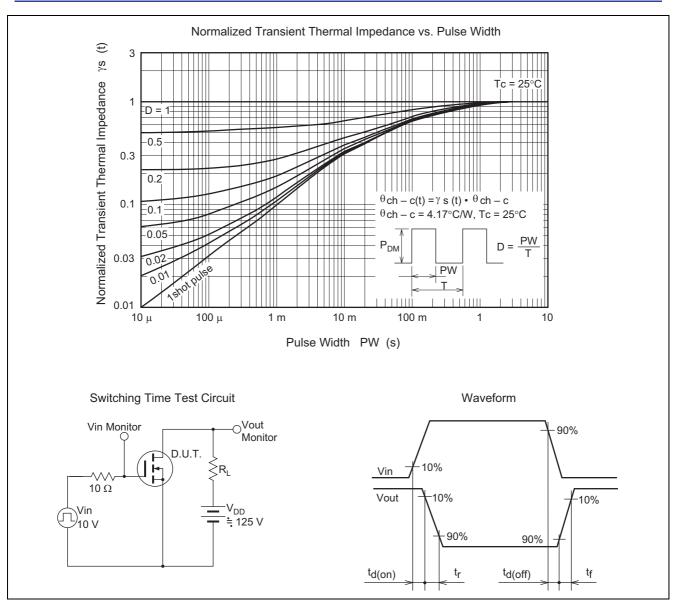
Notes: 4. Pulse test

## **Main Characteristics**

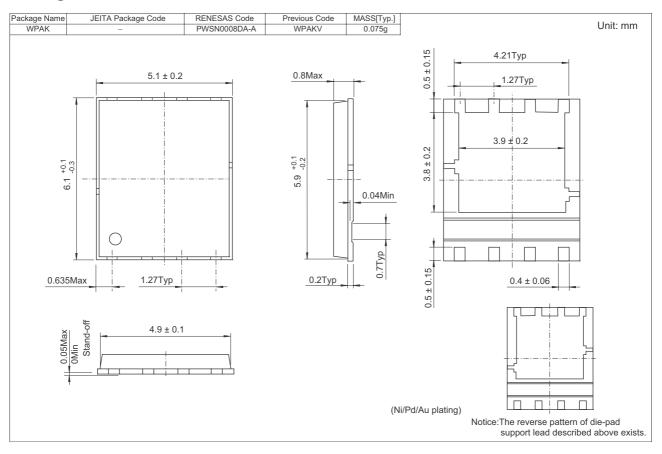


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# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK2555DPA-00-J0	2500 pcs	Taping

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